

BFR193

Low Noise Silicon Bipolar RF Transistor

- For low noise, high-gain amplifiers up to 2 GHz
- For linear broadband amplifiers
- $f_{\rm T}$ = 8 GHz, $NF_{\rm min}$ = 1 dB at 900 MHz
- Pb-free (RoHS compliant) package
- Qualification report according to AEC-Q101 available





ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration			Package
BFR193	RCs	1 = B	2 = E	3 = C	SOT23

Maximum Ratings at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit	
Collector-emitter voltage	V _{CEO}	12	V	
Collector-emitter voltage	V _{CES}	20		
Collector-base voltage	V _{CBO}	20		
Emitter-base voltage	V _{EBO}	2		
Collector current	Ι _C	80	mA	
Base current	I _B	10		
Total power dissipation ¹⁾	P _{tot}	580	mW	
<i>T</i> _S ≤ 69°C				
Junction temperature	TJ	150	°C	
Storage temperature	T _{Stg}	-55 150		
	• • •		•	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R _{thJS}	140	K/W

 ${}^{1}\mathcal{T}_{S}$ is measured on the collector lead at the soldering point to the pcb

²For calculation of R_{thJS} please refer to Application Note AN077 (Thermal Resistance Calculation)



Parameter	Symbol	Values			Unit
		min.	typ.	max.]
DC Characteristics				•	
Collector-emitter breakdown voltage	V _{(BR)CEO}	12	-	-	V
<i>I</i> _C = 1 mA, <i>I</i> _B = 0					
Collector-emitter cutoff current	I _{CES}	-	-	100	μA
$V_{\rm CE}$ = 20 V, $V_{\rm BE}$ = 0					
Collector-base cutoff current	I _{CBO}	-	-	100	nA
$V_{\rm CB}$ = 10 V, $I_{\rm E}$ = 0					
Emitter-base cutoff current	I _{EBO}	-	-	1	μA
<i>V</i> _{EB} = 1 V, <i>I</i> _C = 0					
DC current gain	h _{FE}	70	100	140	-
$I_{\rm C}$ = 30 mA, $V_{\rm CE}$ = 8 V, pulse measured					

Electrical Characteristics at T_A = 25 °C, unless otherwise specified



Parameter	Symbol	Values		Unit	
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency	f _T	6	8	-	GHz
<i>I</i> _C = 50 mA, <i>V</i> _{CE} = 8 V, <i>f</i> = 500 MHz					
Collector-base capacitance	C _{cb}	-	0.66	1	pF
$V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$,					
emitter grounded					
Collector emitter capacitance	C _{ce}	-	0.28	-	
$V_{CE} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$,					
base grounded					
Emitter-base capacitance	C _{eb}	-	2.25	-	
$V_{\rm EB}$ = 0.5 V, f = 1 MHz, $V_{\rm CB}$ = 0 ,					
collector grounded					
Minimum noise figure	NF _{min}				dB
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$,					
<i>f</i> = 900 MHz		-	1	-	
<i>f</i> = 1.8		-	1.6	-	
Power gain, maximum available ¹⁾	G _{ma}				
$I_{\rm C}$ = 30 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt,}$ $Z_{\rm L}$ = $Z_{\rm Lopt}$,					
<i>f</i> = 900 MHz		-	15	-	
<i>f</i> = 1.8 GHz		-	10	-	
Transducer gain	S _{21e} ²				dB
$I_{\rm C}$ = 30 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,					
<i>f</i> = 900 MHz		-	13	-	
<i>f</i> = 1.8 GHz		-	7.5	-	
Third order intercept point at output ²⁾	IP ₃	-	30	-	dBm
$I_{\rm C}$ = 30 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,					
<i>f</i> = 0.9 GHz					
1dB Compression point	P _{-1dB}	-	13	-	
$I_{\rm C}$ = 30 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,					
<i>f</i> = 0.9 GHz					

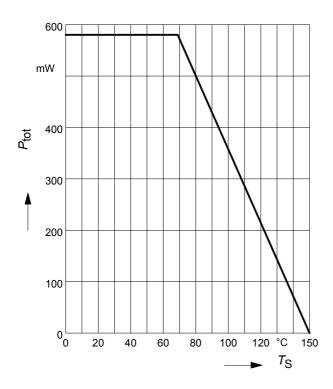
Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

 ${}^{1}G_{\text{ma}} = |S_{21} / S_{12}| (k - (k^{2} - 1)^{1/2})$

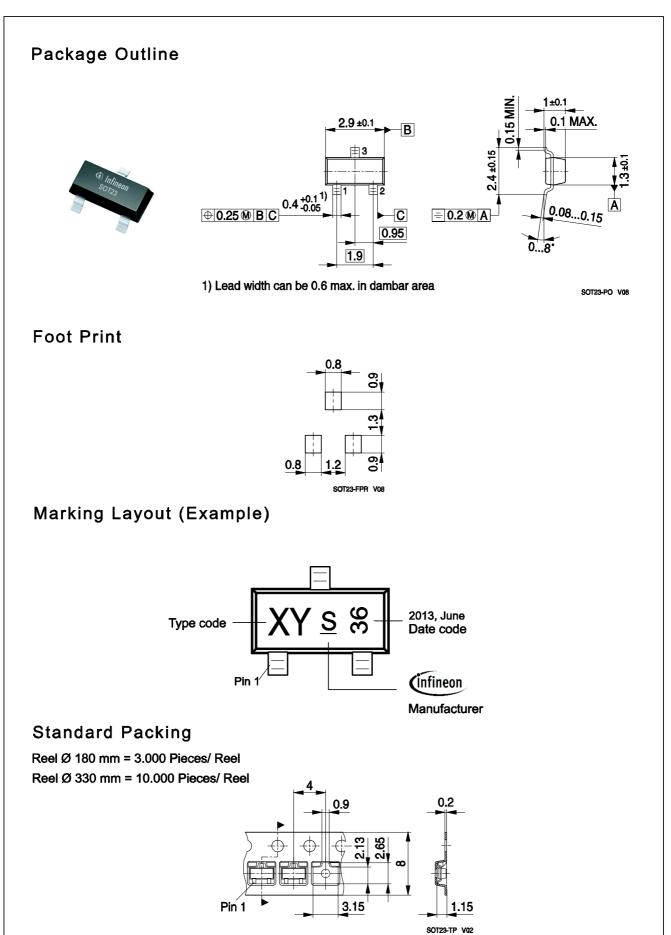
 2 IP3 value depends on termination of all intermodulation frequency components. Termination used for this measurement is 50 Ω from 0.2 MHz to 12 GHz



Total power dissipation $P_{tot} = f(T_S)$











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